**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

## 2. Features and benefits

- · Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drive circuits
- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- · Home appliances
- · Industrial process control
- Low power AC Fan controllers

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions  | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |   | -   | -   | 600 | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>lead</sub> ≤ 45 °C; <u>Fig. 1</u> ;<br><u>Fig. 2</u> ; <u>Fig. 3</u>       | -   | -   | 1   | Α    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)}$ = 25 °C;<br>$t_p$ = 20 ms; Fig. 4; Fig. 5                           | -   | -   | 8   | Α    |
|                     |  | full sine wave; $T_{j(init)}$ = 25 °C;<br>$t_p$ = 16.7 ms   | -   | -   | 8.5 | Α    |
| Tj                  | junction temperature                     |   | -   | -   | 125 | °C   |
| Static chara        | acteristics                              |   |     |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$            | -   | -   | 3   | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$           | -   | -   | 3   | mA   |
|                     |  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$<br>$T_i = 25 ^{\circ}\text{C}; Fig. 7$ | -   | -   | 3   | mA   |

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| Symbol                | Parameter                             | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|-----|-----|-----|------|
|                       |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$<br>$T_j = 25 \text{ °C; } Fig. 7$                               | -   | -   | 5   | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>  | -   | -   | 7   | mA   |
| $V_{T}$               | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>  | -   | 1.3 | 1.6 | V    |
| Dynamic ch            | naracteristics                        |   |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12 | 10  | -   | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 110 °C; $dI_{com}/dt$ = 0.44 A/ms; $I_T$ = 1 A; gate open circuit                            | 0.5 | -   | -   | V/µs |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description     | Simplified outline | Graphic symbol |
|-----|--------|-----------------|--------------------|----------------|
| 1   | T2     | main terminal 2 |                    | T2             |
| 2   | G      | gate            |                    | G<br>sym051    |
| 3   | T1     | main terminal 1 | TO-92 (SOT54)      | symosi         |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number |         | Package |   |         |  |  |  |  |
|-------------|---------|---------|---|---------|--|--|--|--|
|             |         | Name    | Description   | Version |  |  |  |  |
|             | Z0103MA | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |  |  |  |  |

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## 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                                | Conditions   | Min | Max  | Unit |
|---------------------|--|--|-----|------|------|
| $V_{DRM}$           | repetitive peak off-state voltage        |  | -   | 600  | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>lead</sub> ≤ 45 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | -   | 1    | Α    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5                     | -   | 8    | А    |
|                     |  | full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms                   | -   | 8.5  | Α    |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing              | t <sub>p</sub> = 10 ms; SIN  | -   | 0.32 | A²s  |
| dl <sub>T</sub> /dt | rate of rise of on-state current         | I <sub>G</sub> = 20 mA; T2+ G+   | -   | 50   | A/µs |
|                     |  | I <sub>G</sub> = 20 mA; T2+ G-   | -   | 50   | A/µs |
|                     |  | I <sub>G</sub> = 20 mA; T2- G-   | -   | 50   | A/µs |
|                     |  | I <sub>G</sub> = 20 mA; T2- G+   | -   | 20   | A/µs |
| I <sub>GM</sub>     | peak gate current                        |  | -   | 1    | Α    |
| P <sub>GM</sub>     | peak gate power                          |  | -   | 2    | W    |
| P <sub>G(AV)</sub>  | average gate power                       | over any 20 ms period  | -   | 0.1  | W    |
| T <sub>stg</sub>    | storage temperature                      |  | -40 | 150  | °C   |
| Tj                  | junction temperature                     |  | -   | 125  | °C   |

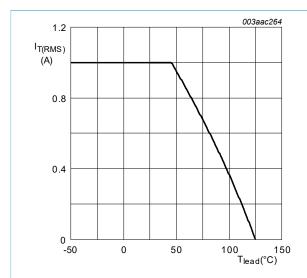


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

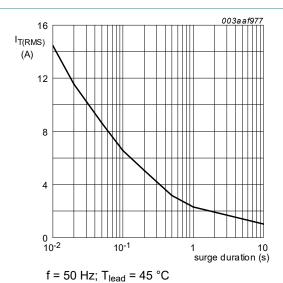


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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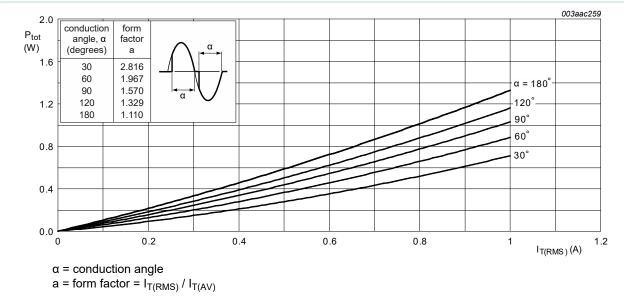


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

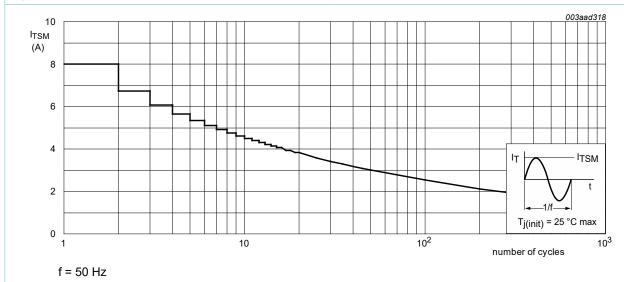
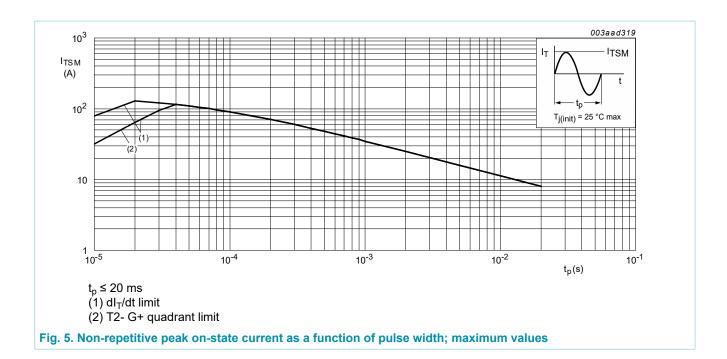


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

| Symbol                  | Parameter  | Conditions   | Min | Тур | Max | Unit |
|-------------------------|--|--|-----|-----|-----|------|
| R <sub>th(j-lead)</sub> | thermal resistance from junction to lead                   | full cycle; Fig. 6   | -   | -   | 60  | K/W  |
| $R_{th(j-a)}$           | thermal resistance<br>from junction to<br>ambient free air | full cycle; printed circuit board mounted;<br>lead length = 4 mm | -   | 150 | -   | K/W  |

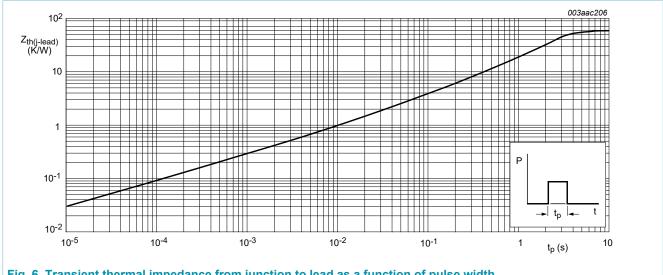


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

#### **Table 6. Characteristics**

| Symbol                | Parameter                             | Conditions   | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|-----|-----|-----|------|
| Static chara          | acteristics                           |  |     |     |     | ,    |
| I <sub>GT</sub>       | gate trigger current                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      | -   | -   | 3   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      | -   | -   | 3   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      | -   | -   | 3   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                      | -   | -   | 5   | mA   |
| լ                     | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 °C; Fig. 8$   | -   | -   | 7   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                  | -   | -   | 15  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$ | -   | -   | 7   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$ | -   | -   | 7   | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>   | -   | -   | 7   | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -   | 1.3 | 1.6 | V    |
| $V_{GT}$              | gate trigger voltage                  | $V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C;<br>Fig. 11   | -   | -   | 1   | V    |
|                       |                                       | $V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 °C;$<br>Fig. 11   | 0.2 | -   | -   | V    |
| l <sub>D</sub>        | off-state current                     | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -   | -   | 0.5 | mA   |
| Dynamic ch            | naracteristics                        |  |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12  | 10  | -   | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 110 °C; $dI_{com}/$<br>dt = 0.44 A/ms; $I_T$ = 1 A; gate open<br>circuit                      | 0.5 | -   | -   | V/µs |

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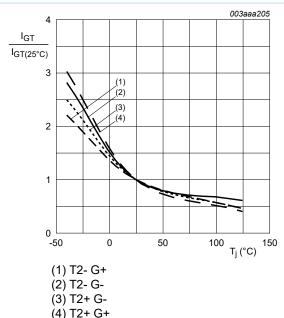
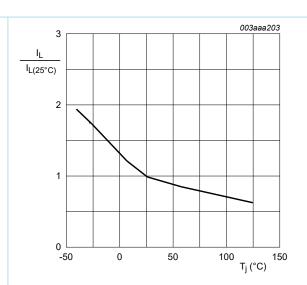


Fig. 8. Normalized latching current as a function of junction temperature (4) T2+ G+

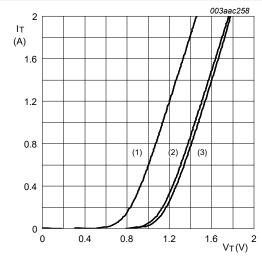


003aaa204 3  $\mathsf{I}_\mathsf{H}$ I<sub>H(25°C)</sub> 2 -50 50 T<sub>j</sub> (°C)

Fig. 7. Normalized gate trigger current as a function of

junction temperature

Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$  $R_s = 0.31 \Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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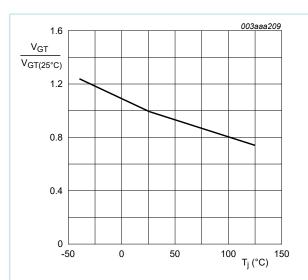


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

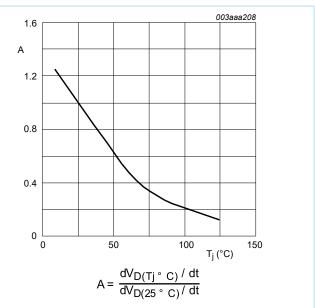
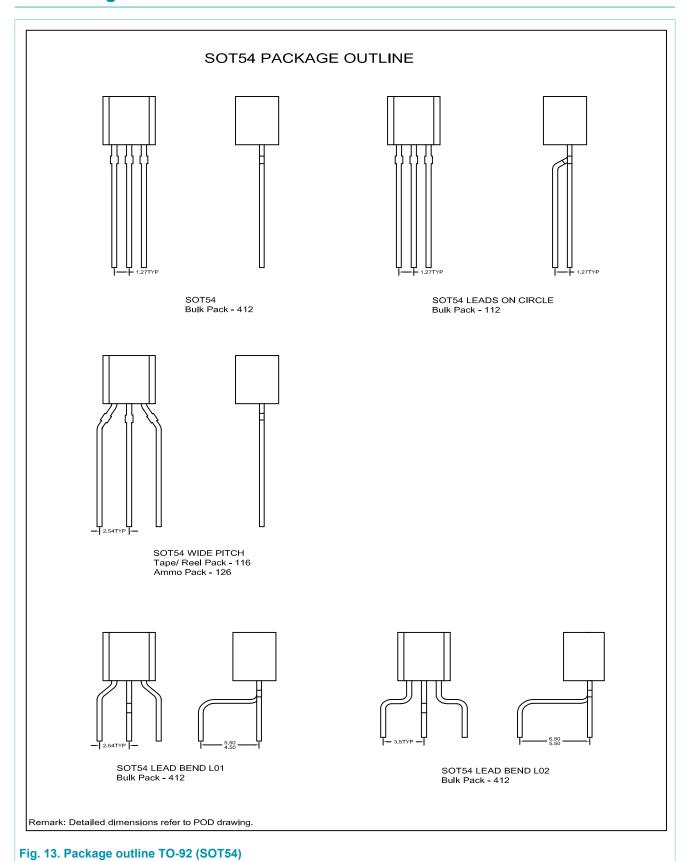


Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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# 10. Package outline



70402848

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## 11. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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